

AMENDMENTS

In the Claims:

Claim 1 (Canceled)

Claim 2 (Amended): A method as claimed in Claim 4 17, wherein the drying process is accomplished by supplying dry gas to the substrate to be processed.

Claim 3 (Amended): A method as claimed in Claim 4 17, wherein the drying process is accomplished by rotating the substrate to be processed.

Claim 4 (Canceled)

Claim 5 (Canceled)

Claim 6 (Amended): A substrate-surface processing method as claimed in Claim 5 20, wherein the drying process for the substrate having the resist pattern formed thereon is accomplished by supplying dry gas to the substrate to be processed.

Claim 7 (Amended): A substrate-surface processing method as claimed in Claim 5 20, wherein the drying process for the substrate having the resist pattern formed thereon is accomplished by rotating the substrate to be processed.

Claims 8-16 (Withdrawn)

Claim 17 (New): A method of processing a surface of a substrate to be processed, the method comprising:

an etching process to supply the substrate having a resist pattern formed thereon with a chemical liquid thereby to remove an oxidation film on the surface of the substrate therefrom;

a rinsing process to supply the substrate with a rinsing liquid thereby to wash the surface of the substrate;

a hydrophilic process to supply the substrate with an ozone water having a concentration ranging from 0.5 to 10 PPM, thereby to form an oxidation film having a thickness ranging from 6 to 10 Å on the surface of the substrate for providing hydrophilicity therefor; and

a drying process to eliminate moisture adhering to the surface of the substrate.

Claim 18 (New): A method as claimed in Claim 17, wherein the rinsing process and the hydrophilic process are carried out in the same processing container, the ozone water having a concentration ranging from 0.5 to 10 PPM being made by continuously adding an ozone water to a rinsing liquid after the rinsing process.

Claim 19 (New): A method as claimed in Claim 18, wherein continuously adding the ozone water to the rinsing liquid is realized by the way that a line for providing an ozone water is connected with a line for providing a rinsing liquid.

Claim 20 (New): A substrate-surface processing method for sorting out a substrate having a resist pattern formed thereon from another substrate having no resist pattern formed thereon and further applying different processes to the substrates selectively,

the method comprising, for the substrate having the resist pattern formed thereon:

an etching process to supply the substrate with a chemical liquid thereby to remove an oxidation film on the surface of the substrate therefrom;

a rinsing process to supply the substrate with a rinsing liquid thereby to wash the surface of the substrate;

a hydrophilic process to supply the substrate with an ozone water thereby to form an oxidation film on the surface of the substrate for hydrophilicity thereof; and

a drying process to eliminate moisture adhering to the surface of the substrate;

the method comprising, for the substrate having no resist pattern formed thereon:

an etching process to supply the substrate having no resist pattern formed thereon with a chemical liquid thereby to remove an oxidation film on the surface of the substrate therefrom;

a rinsing process to supply the substrate with a rinsing liquid thereby to wash the surface of the substrate; and

a drying process to supply the substrate with a dry solvent thereby to eliminate moisture adhering to the surface of the substrate,

wherein the method for the substrate having the resist pattern formed thereon or the method for the substrate having no resist pattern formed thereon is carried out selectively in a same processing container.

Claim 21 (New): A substrate-surface processing method as claimed in Claim 20,
wherein the ozone water in the hydrophilic process has a concentration ranging from 0.5 to 10
PPM, the oxidation film formed on the surface of the substrate having a thickness ranging from 6
to 10 Å.